

*Gunter Semiconductor GmbH*

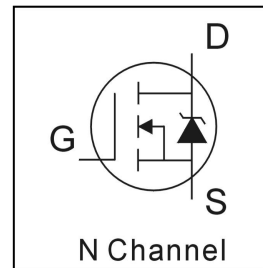
**GFC120**

**N Channel Power MOSFET**

**Chip Specification**

**General Description:**

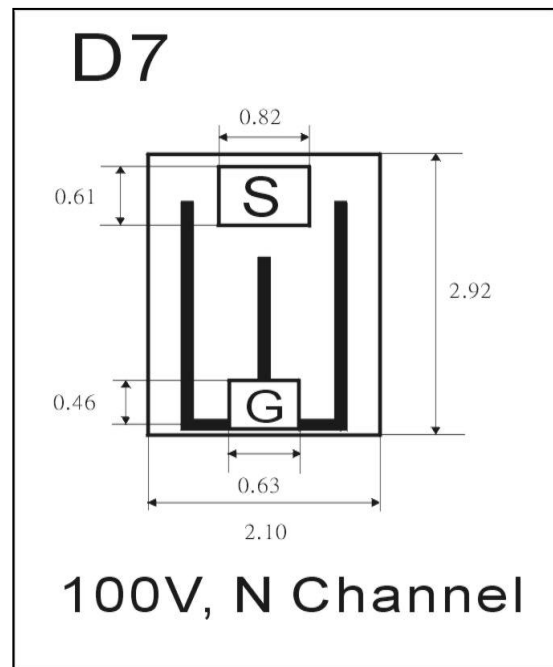
- \* Advanced Process Technology
- \* Dynamic dV/dt Rating
- \* **175°C Operating Temperature**
- \* **Fast Switching**
- \* **Fully Avalanche Rated**



N Channel

**Mechanical Data:**

<b>D7</b>	
Dimension	<b>2.1mm x 2.92mm</b>
Thickness:	<b>400 μm</b>
Metallization:	
Top :	<b>Al</b>
Backside :	<b>CrNiAg / Au</b>
Suggested Bonding Conditions:	
Die Mounting:	<b>Solder Perform</b>
	<b>95/5 PbSn or 92.5/2.5/5 PbAgIn</b>
Source Bonding Wire:	<b>8 mil Al</b>



**Absolute Maximum Rating**

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	100	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.27	Ω	VGS=10V, ID=5.5A
Continuous Drain current ( in target package)	ID@25°C	9.2	A	VGS=10V
Continuous Drain current ( in target package)	ID@100°C	6.5	A	VGS=10V
Operation Junction	Tj	-55~175	°C	
Storage Temperature	TSTR	-55~175	°C	

**Target Device: IRF720**

TO-220AB

Pd

60

W

@Tc=25°C

